SGS-THOMSON MICROELECTRONICS

APPLICATION NOTE

B. RIVET

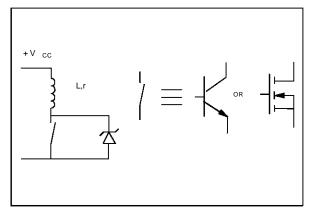
TRANSISTOR PROTECTION BY TRANSIL : DISSIPATION POWER AND SURGE CURRENT DURATION

I - INTRODUCTION

In a great number of applications, we find the diagram FIG.1 where a TRANSIL is used to protect a switch which controls an inductive load. The switch can be a bipolar or a MOS transistor.

The purpose of this paper is to calculate the dissipated power in the Transil and the pulse current duration.

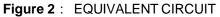
Figure 1 : BASIC DIAGRAM

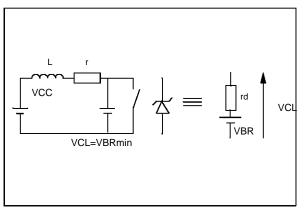


II - CIRCUIT MODELISATION

When the switch turns off we use the equivalent circuit represented FIG.2.

The worst case is to consider $V_{CL} = V_{BR}$ min. This hypothesis will be used in all formulas.





 V_{CL} : clamping voltage V_{BR} : breakdown voltage rd : apparent resistance

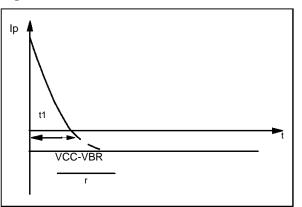
III - CURRENT IN THE TRANSIL

We can express the current i through the TRANSIL by the following formula :

$$i = (Ip + \frac{V_{BR}min - V_{CC}}{r})exp(-r\frac{t}{L}) + (\frac{V_{BR}min - V_{CC}}{r})$$

Ip is the current through the coil when the transistor switches off. The FIG.3 shows the current variation versus time.

Figure 3 : CURRENT WAVEFORM



t1 can be calculated by

$$t1 = -\frac{L}{r} \ln \left(\frac{V_{BR}min - V_{CC}}{V_{BR}min - V_{CC} - rlp} \right)$$

IV - TRANSIL POWER DISSIPATION

We can consider two cases, single pulse operation and repetitive pulses operation.

a) Single pulse operation

In this case, in order to define a TRANSIL we need peak power Pp and the pulse current standard duration tp.

Pp is given by

 $Pp = V_{BR} \min x Ip$

If we assimilate the pulse current with a triangle the standard exponential pulse duration tp is calculated by the formula :

$$tp = -\left(\frac{1,4L}{2r}\right) \ln\left(\frac{V_{BR}\min-V_{CC}}{V_{BR}\min-V_{CC}+rlp}\right)$$

The energy in the Transil can be expressed by :

$$W = \frac{V_{BR}\min L}{r} [I_{P+(\frac{V_{BR}\min - V_{CC}}{r})} I_{P+(\frac{V_{BR}\min - V_{CC}}{r})}]$$

When r tends to zero we find :

$$W = \frac{1}{2} LIp^2 \left(\frac{V_{BR} \min}{V_{BR} \min - V_{CC}} \right)$$

b) Repetitive pulses operation

In repetitive pulse operation the power dissipation can be calculated by the following formula.

 $P = F x \frac{V_{BR}min.L}{r} [I_{P} + (\frac{V_{BR}min-V_{CC}}{r}) I_{N} (\frac{V_{BR}min-V_{CC}}{V_{BR}min-V_{CC} + rI_{P}})]$

When r tends to zero we find :

$$P = \frac{1}{2} LFIp^2 \left(\frac{VBRmin}{VBRmin-VCC} \right)$$

Where F is the commutation frequency.

V - EXAMPLE OF APPLICATION

Commutation of a coil supplied by a battery. The different parameters of the application are :

 $V_{CC} = 14V$ L = 10mH r = 3 0hms Ip = 4A

TRANSIL : 1.5KE36P $V_{BR}min = 34.2V$ (cf data sheet)

a) Single pulse

We find

$$tp = -\left(\frac{-1.4.10.10^{-5}}{2x3}\right) \ln\left(\frac{34.2-14}{34.2-14+3x4}\right)$$

tp = 1.08ms

The data sheet gives Pp 1500W for tp = 1.08ms then this 1.5KE36P can be used in this application.

b) Repetitive pulse operation

The commutation frequency is equal to 10HZ so

$$P = 10x \left(\frac{34.2x10.10^{-3}}{3}\right) \left[4 + \left(\frac{34.2 - 14}{3}\right) \ln \left(\frac{34.2 - 14}{34.2 - 14 + 3x4}\right)\right]$$

= 980mW

Rth = 75° C/W and Tj max. = 175° C

So $Tj = P \times Rth + Tamb.max$.

With Tamb.max. = 50° C we find :

Tj = 0.98 x 75 + 50 = 123.5°C < Tj max

So we can also use this Transil in repetitive pulse operation.

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